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(57) Abstract:

ABSTRACT Dielectric Modulated Heterojunction Vertical TFET Biosensor for Autism Spectrum Disorder Biomarker Detection The present invention relates to a dielectric modulated heterojunction vertical TFET biosensor is for initial stage screening of Austism Spectrum Disorder, comprising of a silicon substrate, a nanocavity, a dual dielectric layer, and at least three gates to provide specific and sensitive screening. Reference Fig 1

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